

## HZN6.8ZMFA

Silicon Planar Zener Diode for Surge Absorb

REJ03G0032-0100Z  
(Previous: ADE-208-1456)  
Rev.1.00  
May.08. 2003

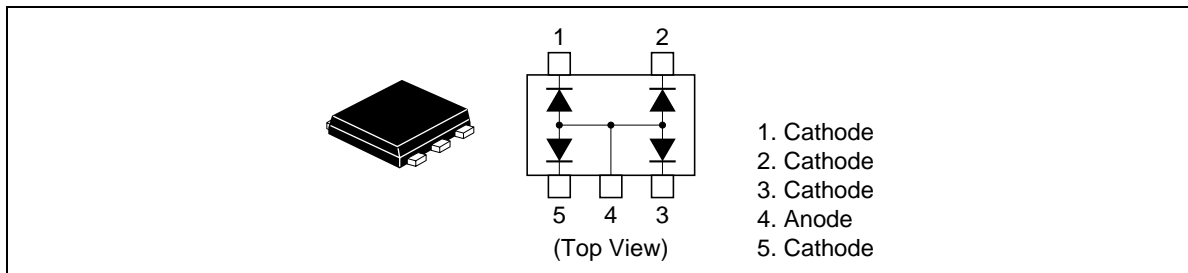
### Features

- HZN6.8ZMFA has four devices in a monolithic, and can absorb surge.
- VSON-5T Package is suitable for high density surface mounting.

### Ordering Information

Type No.	Laser Mark	Package Code
HZN6.8ZMFA	68>(* : Let to Month Code)	VSON-5T

### Pin Arrangement



## HZN6.8ZMFA

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### Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Power dissipation	Pd * <sup>1</sup>	150	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note: 1. Four device total, See Fig.2.

### Electrical Characteristics \*<sup>1</sup>

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Zener voltage	V <sub>z</sub>	6.47	—	7.00	V	I <sub>z</sub> = 5 mA, 40 ms pulse
Reverse current	I <sub>R</sub>	—	—	0.5	μA	V <sub>R</sub> = 3.5 V
Capacitance	C	—	—	25	pF	V <sub>R</sub> = 0 V, f = 1 MHz
Dynamic resistance	r <sub>d</sub>	—	—	30	Ω	I <sub>z</sub> = 5 mA
ESD-Capability * <sup>2</sup> * <sup>3</sup>	—	25	—	—	kV	C = 150 pF, R = 330 Ω, Both forward and reverse direction 10 pulse

Notes: 1. Per one device.

2. Failure criterion ; I<sub>R</sub> > 0.5 μA at V<sub>R</sub> = 3.5 V.

3. Between cathode and anode.

### Month Code

Month of Manufacture	Month Code	Month of Manufacture	Month Code
January	A	July	G
February	B	August	H
March	C	September	J
April	D	October	K
May	E	November	L
June	F	December	M

Main Characteristic

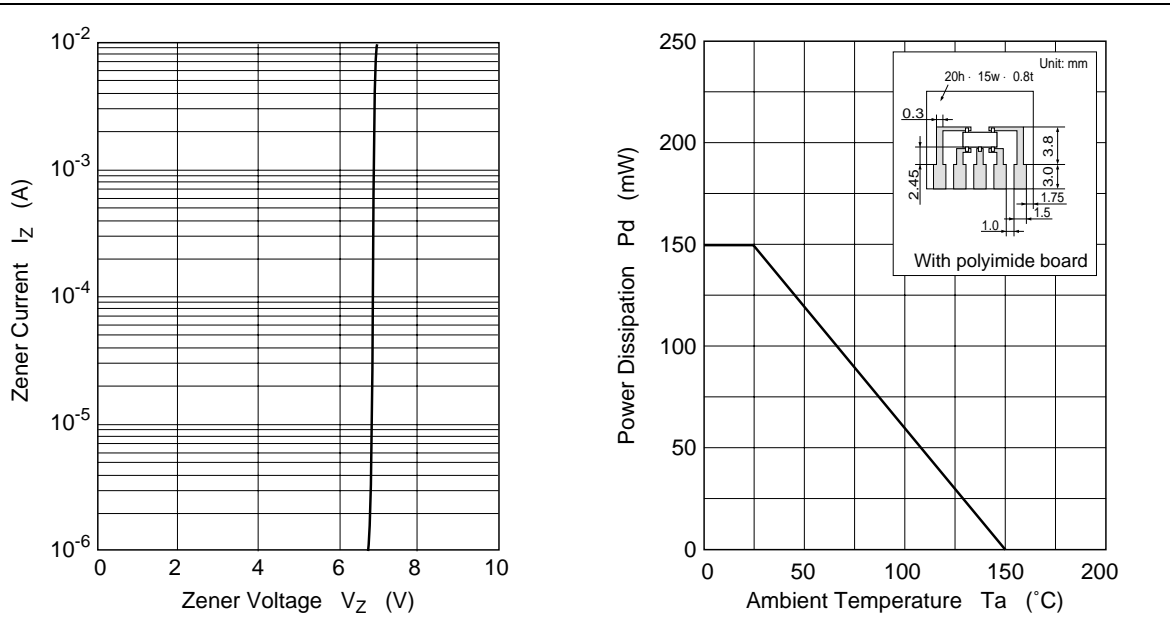


Fig.1 Zener current vs. Zener voltage

Fig.2 Power Dissipation vs. Ambient Temperature

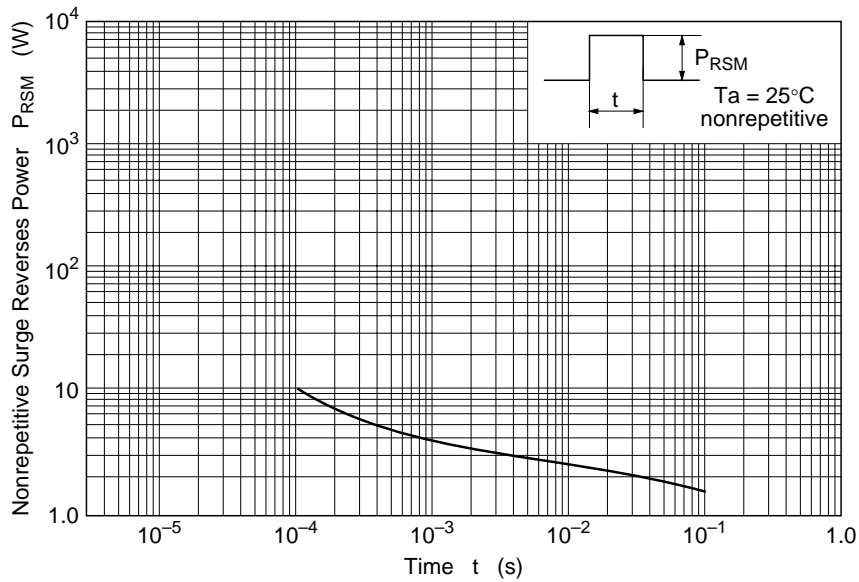
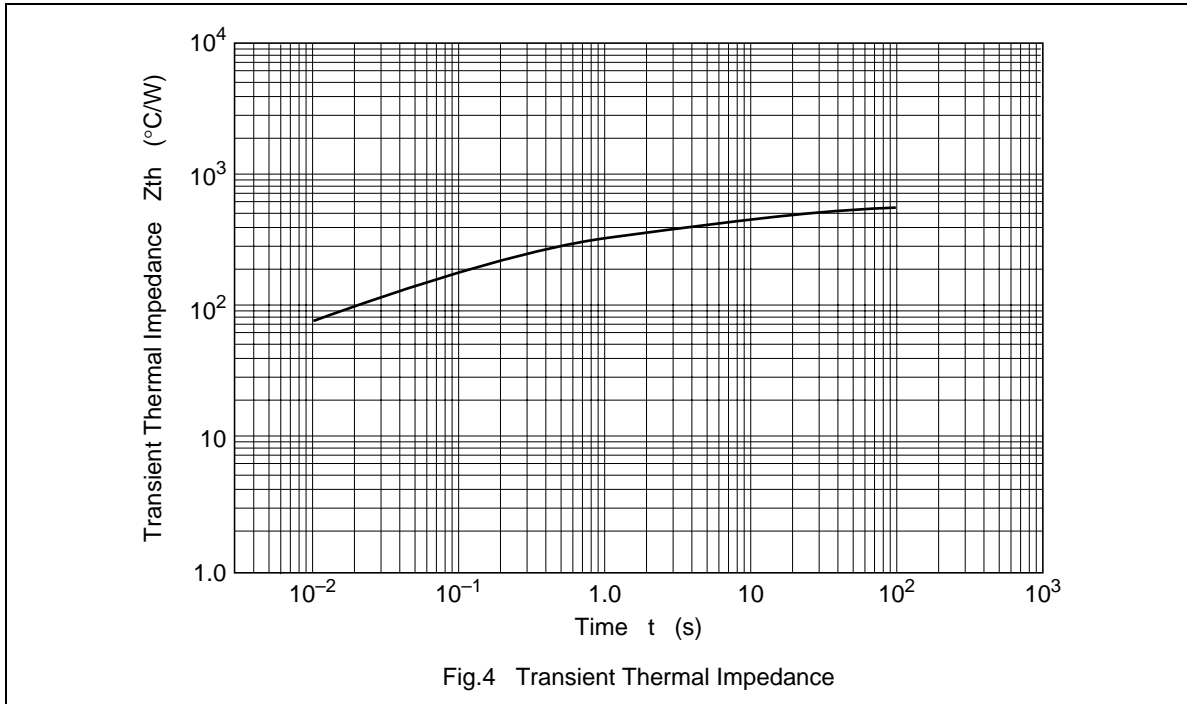
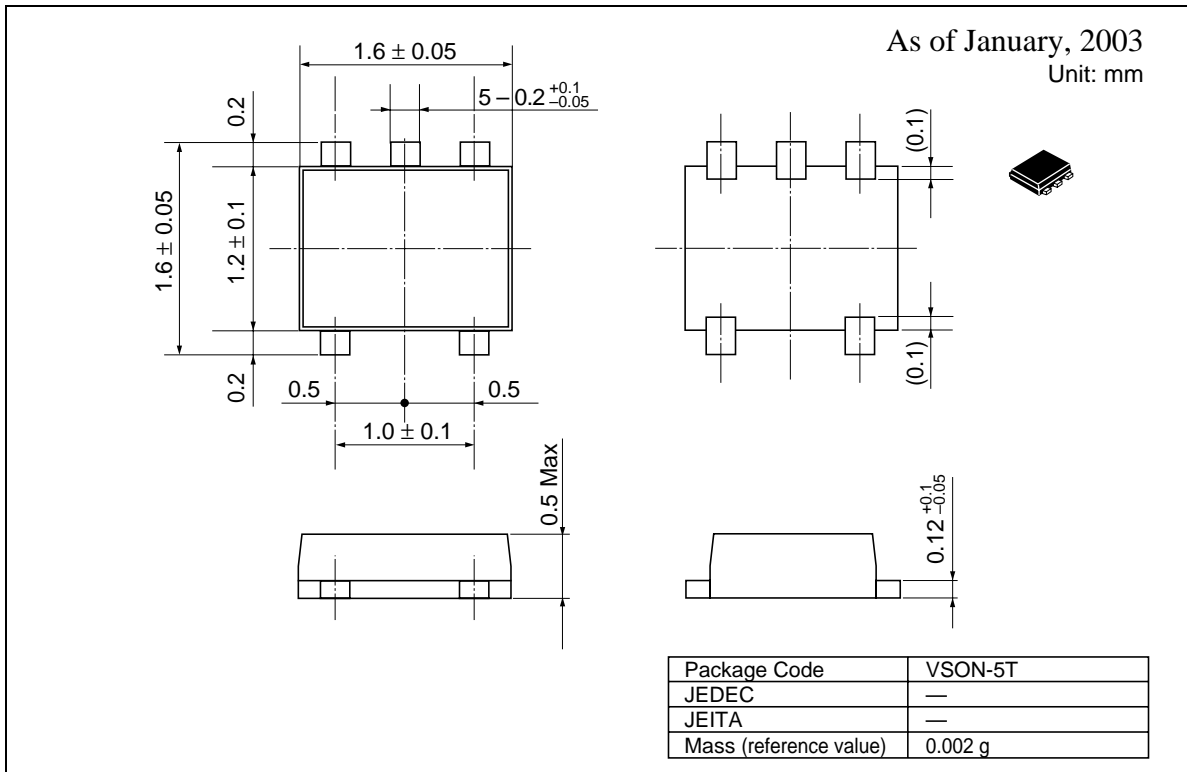


Fig.3 Surge Reverse Power Ratings

Main Characteristic (cont.)



Package Dimensions



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